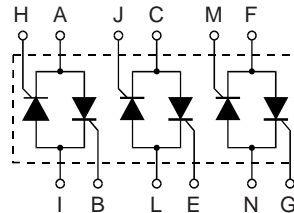


AC Controller Modules

$I_{RMS} = 3 \times 35 \text{ A}$
 $V_{RRM} = 600-1200 \text{ V}$

Preliminary data

V_{RSM}	V_{RRM}	Type
V_{DSM}	V_{DRM}	
V	V	
700	600	VWO 35-06ho7
900	800	VWO 35-08ho7
1300	1200	VWO 35-12ho7



Symbol	Conditions	Maximum Ratings	
I_{RMS}	$T_C = 85^\circ\text{C}$, (per phase)	35	A
I_{TAVM}	$T_C = 85^\circ\text{C}$; (180° sine ; per thyristor)	16	A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine	200 A
		t = 8.3 ms (60 Hz), sine	210 A
I^2t	$T_{VJ} = T_{VJM}$; $V_R = 0$	t = 10 ms (50 Hz), sine	180 A
		t = 8.3 ms (60 Hz), sine	190 A
I^2t	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine	200 A ² s
		t = 8.3 ms (60 Hz), sine	150 A ² s
$(di/dt)_{cr}$	$T_{VJ} = T_{VJM}$; f = 50Hz, $t_p = 200\mu\text{s}$ $V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.15 \text{ A}$ $di_G/dt = 0.15 \text{ A}/\mu\text{s}$	repetitive, $I_T = 20 \text{ A}$	100 A/ μs
		non repetitive, $I_T = I_{TAVM}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = T_{VJM}$; $R_{GK} = \infty$; method 1 (linear voltage rise)	$V_{DR} = 2/3 V_{DRM}$	500 V/ μs
V_{RGM}		10	V
P_{GM}	$T_{VJ} = T_{VJM}$; $I_T = I_{TAVM}$	$t_p = 30 \mu\text{s}$	$\leq 5 \text{ W}$
		$t_p = 300 \mu\text{s}$	$\leq 2.5 \text{ W}$
P_{GAVM}		0.5	W
T_{VJ}		-40...+125	°C
T_{VJM}		125	°C
T_{sig}		-40...+125	°C
V_{ISOL}	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	t = 1 min	2500 V~
		t = 1 s	3000 V~
M_d	Mounting torque (M4)	1.5 - 2	Nm
		14 - 18	lb.in.
Weight	typ.	18	g

Features

- Thyristor controller for AC (circuit W3C acc. to IEC) for mains frequency
- Soldering connections for PCB mounting
- Isolation voltage 3000 V~
- Planar passivated chips

Applications

- Switching and control of three phase AC circuits
- Softstart AC motor controller
- Solid state switches
- Light and temperature control

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Data according to IEC 60747 refer to a single thyristor/diode unless otherwise stated. IXYS reserves the right to change limits, test conditions and dimensions

Symbol	Conditions	Characteristic Values	
I_{D}, I_{R}	$T_{VJ} = T_{VJM}; V_{R} = V_{RRM}; V_{D} = V_{DRM}$	\leq	5 mA
V_{T}	$I_{T} = 20 \text{ A}; T_{VJ} = 25^{\circ}\text{C}$	\leq	1.6 V
V_{T0}	For power-loss calculations only		0.85 V
r_{T}			27 m Ω
V_{GT}	$V_{D} = 6 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$	\leq	1.5 V
	$T_{VJ} = -40^{\circ}\text{C}$	\leq	2.5 V
I_{GT}	$V_{D} = 6 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$	\leq	25 mA
	$T_{VJ} = -40^{\circ}\text{C}$	\leq	50 mA
V_{GD}	$T_{VJ} = T_{VJM}; V_{D} = \frac{2}{3} V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	3 mA
I_{L}	$T_{VJ} = 25^{\circ}\text{C}; t_{p} = 10 \mu\text{s}$ $I_{G} = 0.1 \text{ A}; di_{G}/dt = 0.1 \text{ A}/\mu\text{s}$	\leq	75 mA
I_{H}	$T_{VJ} = 25^{\circ}\text{C}; V_{D} = 6 \text{ V}; R_{GK} = \infty$	\leq	50 mA
t_{gd}	$T_{VJ} = 25^{\circ}\text{C}; V_{D} = \frac{1}{2} V_{DRM}$ $I_{G} = 0.1 \text{ A}; di_{G}/dt = 0.1 \text{ A}/\mu\text{s}$	\leq	2 μs
R_{thJC}	per thyristor; DC		1.3 K/W
	per module		0.22 K/W
R_{thJK}	per thyristor; DC		1.8 K/W
	per module		0.3 K/W
d_{S}	Creeping distance on surface		11.2 mm
d_{A}	Creepage distance in air		5.0 mm
a	Max. allowable acceleration		50 m/s ²

Dimensions in mm (1 mm = 0.0394")
